# 4V Drive Nch MOS FET **RHK005N03**

#### ●Structure

Silicon N-channel MOS FET

## ● Features

- 1) Low On-resistance.
- 2) High speed switching.

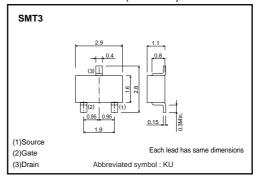
## Applications

Switching

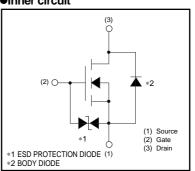
# ●Packaging specifications and hFE

	Package	Taping
Type	Code	T146
	Basic ordering unit (pieces)	3000
RHK005N03	0	

# ●External dimensions (Unit : mm)



## ●Inner circuit



# ● Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		$V_{DSS}$	30	V
Gate-source voltage		V <sub>GSS</sub>	±20	V
Drain current	Continuous	I <sub>D</sub>	±500	mA
	Pulsed	IDP *1	±2.0	Α
Total power dissipation		P <sub>D</sub> *2	200	mW
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

#### ●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	625	°C/W

<sup>\*</sup> Each terminal mounted on a recommended land

<sup>\*1</sup> Pw≤10μs, Duty cycle≤1% \*2 Each terminal mounted on a recommended land

# ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	1	_	±10	μΑ	Vgs= ±20V, Vps=0V
Drain-source breakdown voltage	$V_{(BR)\;DSS}$	30	_	_	٧	I <sub>D</sub> = 1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	1	μΑ	V <sub>DS</sub> = 30V, V <sub>GS</sub> =0V
Gate threshold voltage	V <sub>GS (th)</sub>	1.0	_	2.5	٧	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA
Static drain-source on-state resistance	R <sub>DS (on)</sub> *	_	350	550	$m\Omega$	I <sub>D</sub> = 500mA, V <sub>GS</sub> = 10V
		-	510	720	mΩ	I <sub>D</sub> = 500mA, V <sub>GS</sub> = 4.5V
		-	600	840	mΩ	Ip= 500mA, Vgs= 4V
Forward transfer admittance	Yfs *	0.5	_	_	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 500mA
Input capacitance	Ciss	_	45	_	pF	V <sub>DS</sub> = 10V
Output capacitance	Coss	-	20	_	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	Crss	_	10	_	pF	f=1MHz
Turn-on delay time	t <sub>d (on)</sub> *	-	10	_	ns	V <sub>DD</sub> ≒ 15V
Rise time	tr *	_	10	_	ns	ID= 250mA
Turn-off delay time	t <sub>d (off)</sub> *	-	15	_	ns	V <sub>GS</sub> = 10V R <sub>L</sub> =60Ω
Fall time	t <sub>f</sub> *	_	30	_	ns	R <sub>G</sub> =10Ω

\*Pulsed

# ●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp	_	-	1.2	V	I <sub>S</sub> = 0.16A, V <sub>GS</sub> =0V

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